

# STGW60V60DF, STGWT60V60DF

Trench gate field-stop IGBT, V series 600 V, 60 A very high speed



#### Figure 1. Internal schematic diagram



Datasheet - production data

### Features

- Maximum junction temperature: T<sub>J</sub> = 175 °C
- Tail-less switching off
- V<sub>CE(sat)</sub> = 1.85 V (typ.) @ I<sub>C</sub> = 60 A
- Tight parameters distribution
- Safe paralleling
- Low thermal resistance
- Very fast soft recovery antiparallel diode

## Applications

- Photovoltaic inverters
- Uninterruptible power supply
- Welding
- Power factor correction
- Very high frequency converters

## Description

This device is an IGBT developed using an advanced proprietary trench gate field stop structure. The device is part of the V series of IGBTs, which represent an optimum compromise between conduction and switching losses to maximize the efficiency of very high frequency converters. Furthermore, a positive  $V_{CE(sat)}$  temperature coefficient and very tight parameter distribution result in safer paralleling operation.

Order code	Marking	Package	Packaging
STGW60V60DF	GW60V60DF	TO-247	Tube
STGWT60V60DF	GWT60V60DF	TO-3P	Tube

DocID024154 Rev 6

This is information on a product in full production.

## 1 Electrical ratings

Symbol	Parameter	Value	Unit
V <sub>CES</sub>	Collector-emitter voltage (V <sub>GE</sub> = 0)	600	V
Ι <sub>C</sub>	Continuous collector current at T <sub>C</sub> = 25 °C	80 <sup>(1)</sup>	А
۱ <sub>C</sub>	Continuous collector current at T <sub>C</sub> = 100 °C	60	А
$I_{CP}^{(2)}$	Pulsed collector current	240	А
V <sub>GE</sub>	Gate-emitter voltage	±20	V
۱ <sub>F</sub>	Continuous forward current at $T_C = 25 \text{ °C}$	80 <sup>(1)</sup>	А
۱ <sub>F</sub>	Continuous forward current at $T_C = 100 \text{ °C}$	60	А
I <sub>FP</sub> <sup>(2)</sup>	Pulsed forward current	240	А
P <sub>TOT</sub>	Total dissipation at $T_{C} = 25 \text{ °C}$	375	W
T <sub>STG</sub>	Storage temperature range	- 55 to 150	°C
TJ	Operating junction temperature	- 55 to 175	°C

### Table 2. Absolute maximum ratings

1. Current level is limited by bond wires

2. Pulse width limited by maximum junction temperature.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R <sub>thJC</sub>	Thermal resistance junction-case IGBT	0.4	°C/W
R <sub>thJC</sub>	Thermal resistance junction-case diode	1.14	°C/W
R <sub>thJA</sub>	Thermal resistance junction-ambient	50	°C/W